

• Objective:

- » Explore the possibilities of using Sb-based nanostructure for high-current HEMTs
- » Leverage extreme anisotropy of L-valley masses

• Approach:

- » Use new tight-binding parameters of G. Hegde
- » Use NEMO 5 flexibility in crystal directions, minimal unit cells

• Results / Impact:

- » 2 conference contributions (DRC 2010/2011) in collaboration with M. Rodwell, UCSB
- » Analysis shows extremely good characteristics of GaSb/AlSb [111]-QWs

